

Serial No.: 10/044,493

better condition for allowance and/or appeal. Accordingly, entry of the reply is considered proper.

Favorable reconsideration of the application is respectfully requested in view of the following.

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IN THE CLAIMS:

Please amend claim 1 as follows. Please place claim 20 in independent form as follows. A marked version of the amended claims appears in Appendix A attached hereto.

1. (twice amended) A semiconductor device comprising:

a source and a drain, said source and drain consisting essentially of silicide;

a semiconductor body disposed between the source and the drain;

a gate electrode disposed over the body and defining a channel interposed between the source and the drain; and

a gate dielectric separating the gate electrode and the body, said gate dielectric being made from a material having a relative permittivity of greater than about 10.

20. (amended) A semiconductor device comprising:

a source and a drain, said source and drain consisting essentially of silicide;

a semiconductor body disposed between the source and the drain, wherein a source/body junction is defined by silicide material of the source and semiconductor material of the body and a drain/body junction is defined by silicide material of the drain and semiconductor material of the body;

a gate electrode disposed over the body and defining a channel interposed between the source and the drain; and

a gate dielectric separating the gate electrode and the body, said gate dielectric being made from a material having a relative permittivity greater than about 10.